Power MOSFET –60V, 250mΩ, –1.8A, P-Channel

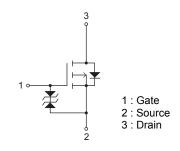


ON Semiconductor®

www.onsemi.com

VDSS	R _{DS} (on) Max	ID Max
	250mΩ@ –10V	
-60V	330mΩ@ –4.5V	-1.8A
	350mΩ@ -4.0V	

ELECTRICAL CONNECTION P-Channel



MARKING





ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Automotive Power MOSFET designed to minimize gate charge and low on resistance. AEC-Q101 qualified MOSFET and PPAP capable suitable for automotive applications.

Features

- 4V drive
- High ESD protection
- Low On-Resistance
- AEC-Q101 qualified and PPAP capable
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- Reverse Battery Protection
- High Side Load Switch
- Automotive Body Controllers

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit	
Drain to Source Voltage	VDSS	-60	V	
Gate to Source Voltage	VGSS	±20	V	
Drain Current (DC) (Note 2)	ID	-1.8	Α	
Drain Current (DC) (Note 3)	טי [-1.7	Α	
Drain Current (Pulse)	IDP		Α	
PW ≤ 10μs, duty cycle ≤ 1%	, , , , , , , , , , , , , , , , , , ,	-7.2	,	
Power Dissipation	ver Dissipation		W	
Ta=25°C(Note 2)	PD	1.2		
Power Dissipation	טין	0.8	W	
Ta=25°C(Note 3)		0.0	٧٧	
Junction Temperature and	Tj, Tstg	-55 to +175	°C	
Storage Temperature	13, 1319	-55 (0 +175		

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Value	Unit
Junction to Ambient	(Note 2)	125		°C/W
	(Note 3)	$R_{ heta}$ JA	182	°C/W

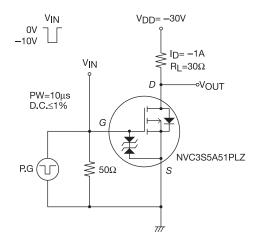
Note 2 : Surface mounted on ceramic substrate(900mm² × 0.8mm). Note 3 : Surface mounted on FR4 board using a 92mm², 1 oz. Cu pad.

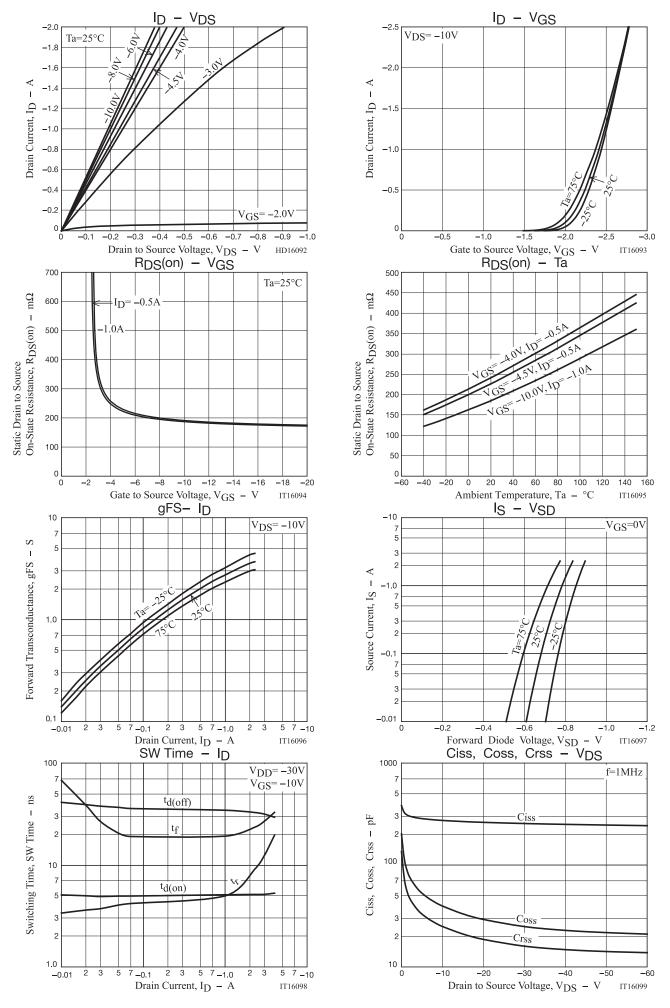
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 4)

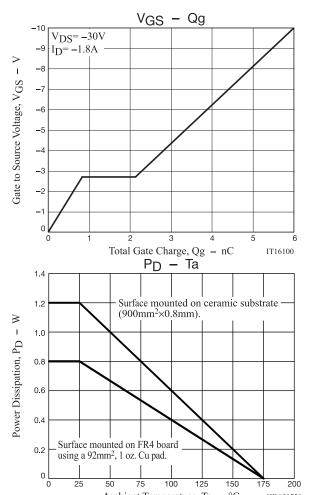
Parameter	Cumbal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	gFS .	V _{DS} =-10V, I _D =-1A		2.7		S
Static Drain to Source On-State Resistance		I _D =-1A, V _G S=-10V		190	250	mΩ
	R _{DS} (on)	I _D =-0.5A, V _G S=-4.5V		235	330	mΩ
		I _D =-0.5A, V _G S=-4V		250	350	mΩ
Input Capacitance	Ciss			262		pF
Output Capacitance	Coss	V _{DS} =–20V, f=1MHz		29		pF
Reverse Transfer Capacitance	Crss			19		pF
Turn-ON Delay Time	t _d (on)			5.1		ns
Rise Time	t _r	Soo Fig 1		5.4		ns
Turn-OFF Delay Time	t _d (off)	See Fig.1		34		ns
Fall Time	tf			19		ns
Total Gate Charge	Qg			6.0		nC
Gate to Source Charge	Qgs	V _{DS} =-30V, V _{GS} =-10V, I _D =-1.8A		0.83		nC
Gate to Drain "Miller" Charge	Qgd			1.3		nC
Forward Diode Voltage	V _{SD}	I _S =-1.8A, V _{GS} =0V		-0.82	-1.2	V

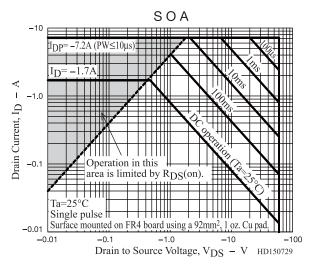
Note 4 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

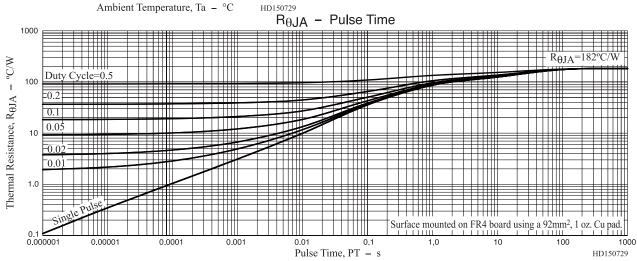
Fig.1 Switching Time Test Circuit







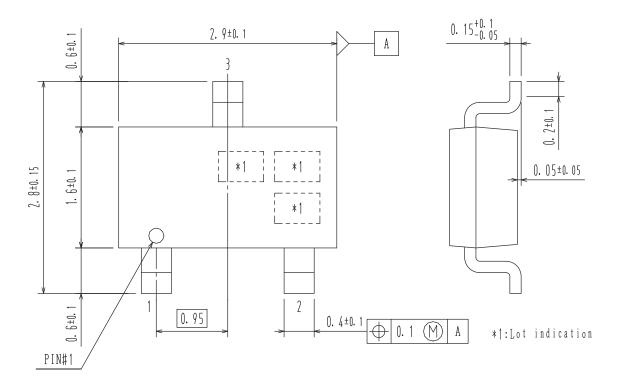


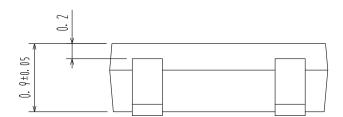


PACKAGE DIMENSIONS

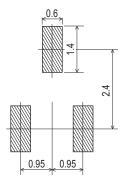
unit: mm

CPH3 CASE 318BA ISSUE O





RECOMMENDED SOLDERING FOOTPRINT



- 1 : Gate 2 : Source
- 3 : Drain

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
NVC3S5A51PLZT1G	WH	CPH3 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the NVC3S5A51PLZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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